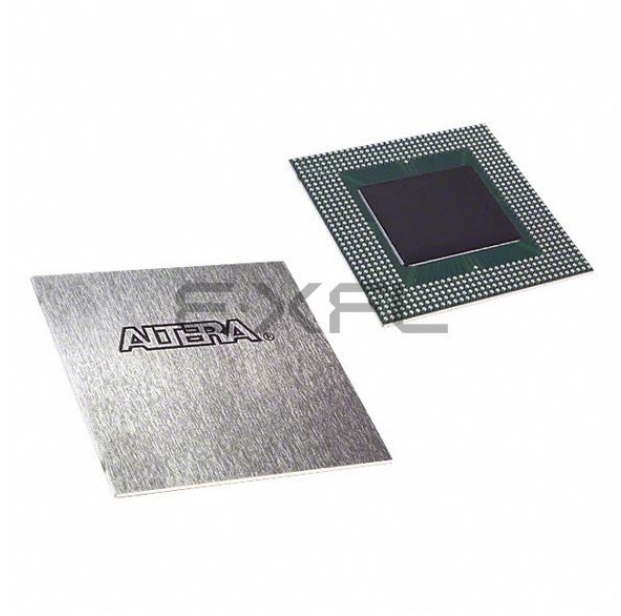


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

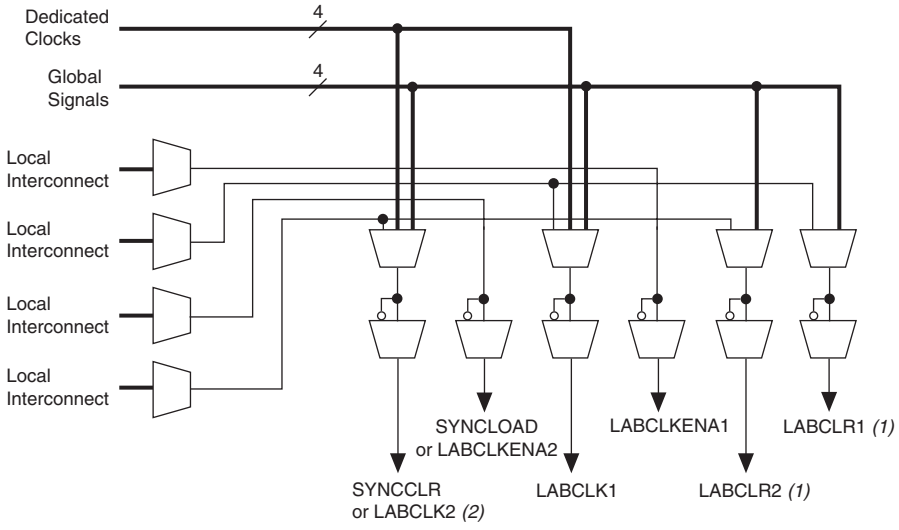
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1664
Number of Logic Elements/Cells	16640
Total RAM Bits	212992
Number of I/O	488
Number of Gates	1052000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	652-BGA
Supplier Device Package	652-BGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k400cb652c9es

The LAB-wide control signals can be generated from the LAB local interconnect, global signals, and dedicated clock pins. The inherent low skew of the FastTrack interconnect enables it to be used for clock distribution. Figure 4 shows the LAB control signal generation circuit.

Figure 4. LAB Control Signal Generation



Notes to Figure 4:

(1) The LABCLR1 and LABCLR2 signals also control asynchronous load and asynchronous preset for LEs within the LAB.

(2) The SYNCCLR signal can be generated by the local interconnect or global signals.

Logic Element

The LE, the smallest unit of logic in the APEX 20KC architecture, is compact and provides efficient logic usage. Each LE contains a four-input LUT, which is a function generator that can quickly implement any function of four variables. In addition, each LE contains a programmable register and carry and cascade chains. Each LE drives the local interconnect, MegaLAB interconnect, and FastTrack interconnect routing structures. See Figure 5.

The APEX 20KC architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. A carry chain supports high-speed arithmetic functions such as counters and adders, while a cascade chain implements wide-input functions such as equality comparators with minimum delay. Carry and cascade chains connect LEs 1 through 10 in an LAB and all LABs in the same MegaLAB structure.

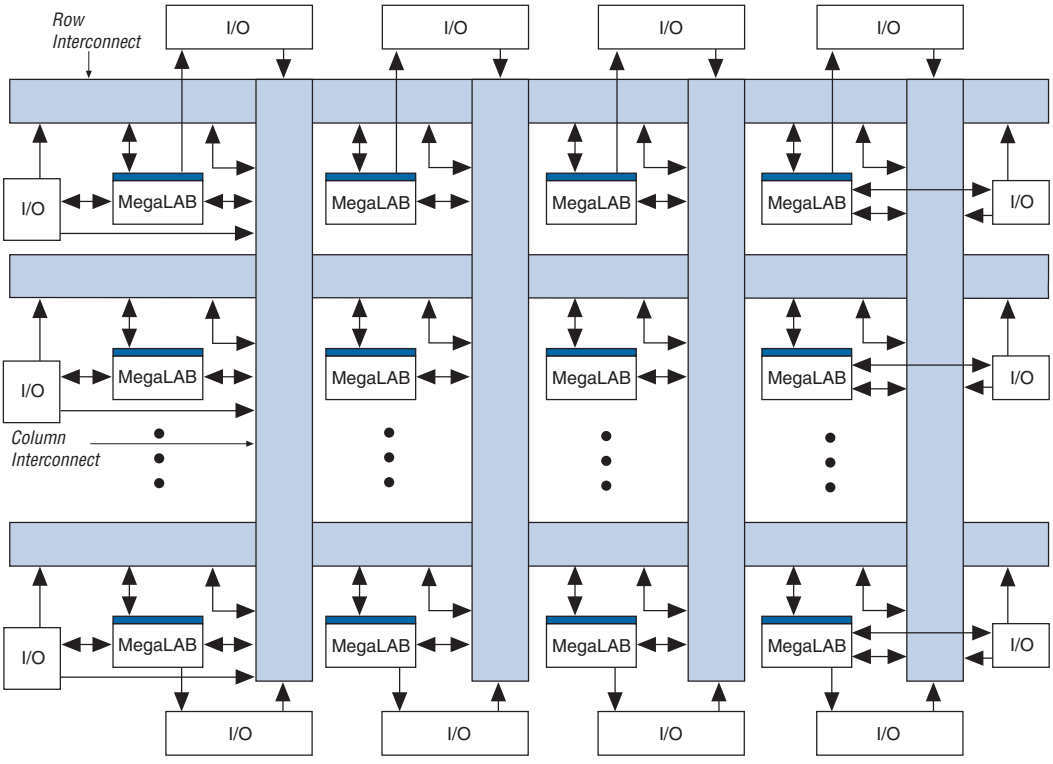
Carry Chain

The carry chain provides a very fast carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the APEX 20KC architecture to implement high-speed counters, adders, and comparators of arbitrary width. Carry chain logic can be created automatically by the Quartus II Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as DesignWare functions from Synopsys and library of parameterized modules (LPM) functions automatically take advantage of carry chains for the appropriate functions.

The Quartus II Compiler creates carry chains longer than ten LEs by automatically linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a MegaLAB structure. A carry chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure.

Figure 6 shows how an *n*-bit full adder can be implemented in *n* + 1 LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is driven onto the local, MegaLAB, or FastTrack interconnect routing structures.

Figure 9. APEX 20KC Interconnect Structure

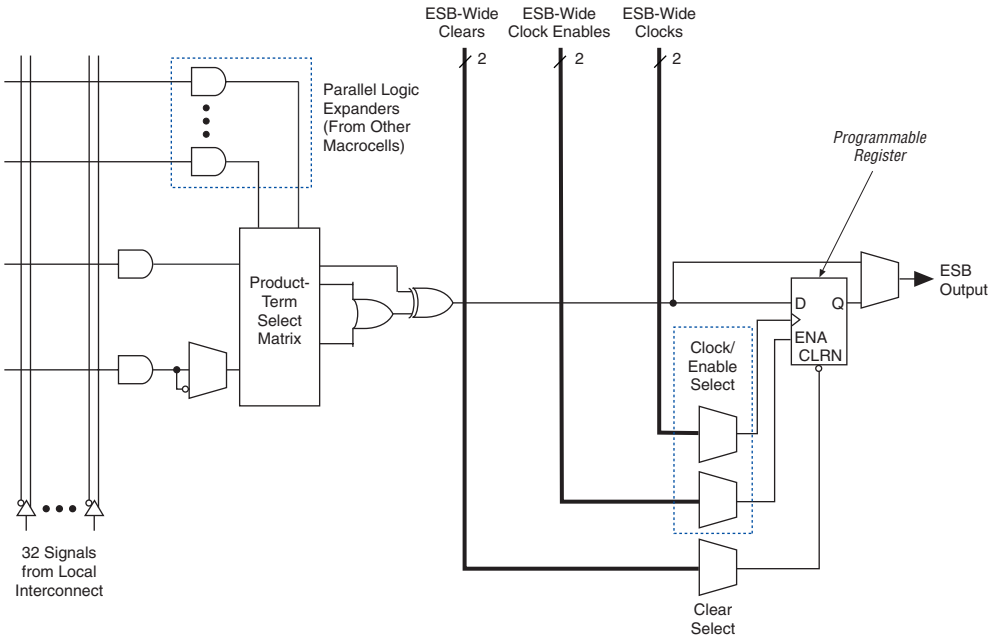


A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack interconnect uses the local interconnect to drive LEs within MegaLAB structures.

Figure 14. APEX 20KC Macrocell



For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

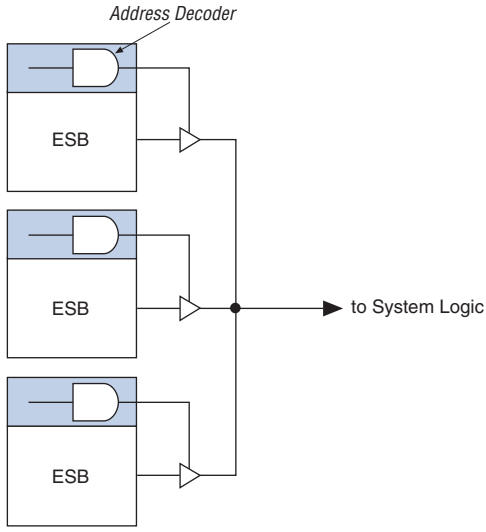
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two ESBs are used to support two simultaneous reads or writes.

The ESB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 19.

Figure 19. APEX 20KC ESB Implementing Dual-Port RAM

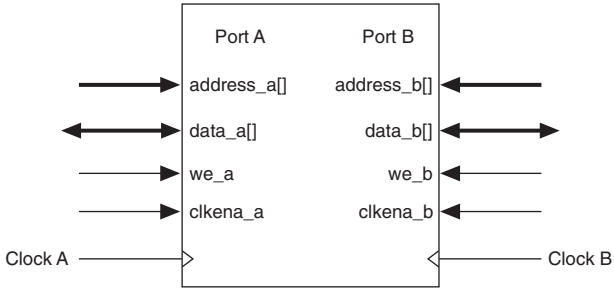
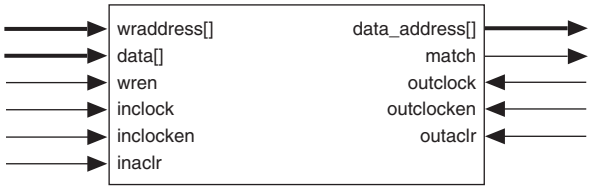


Figure 23. APEX 20KC CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't care" bit can be used as a mask for CAM comparisons; any bit set to "don't care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't care" bits are used, a third clock cycle is required.

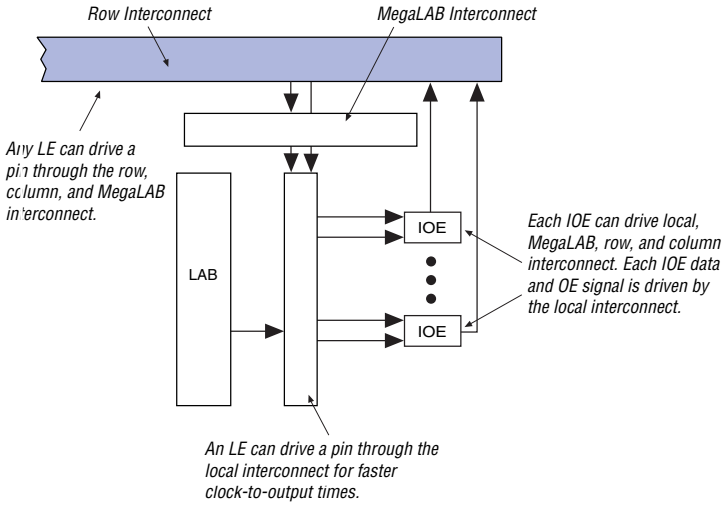
The register in the APEX 20KC IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 25 shows how fast bidirectional I/O pins are implemented in APEX 20KC devices. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Notes to Figure 25:
(1) This programmable delay has four settings: off and three levels of delay.
(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 26 shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect



Advanced I/O Standard Support

APEX 20KC IOEs support the following I/O standards: LVTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.

For more information on I/O standards supported by APEX 20KC devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KC device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL at up to 156 Mbps per channel with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own VCCIO pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate V_{REF} level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K400C and larger APEX 20KC devices support the LVDS interface for data pins (EP20K200C devices support LVDS clock pins, but not data pins). EP20K400C and EP20K600C devices support LVDS for data pins at up to 840 Mbps per channel. EP20K1000C devices support LVDS on 16 channels at up to 750 Mbps.

Each bank can support multiple standards with the same VCCIO for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same VCCIO voltage level. For example, when VCCIO is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used for the LVDS I/O standard, they support all of the other I/O standards. Figure 28 shows the arrangement of the APEX 20KC I/O banks.

Open-drain output pins on APEX 20KC devices (with a series resistor and a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

ClockLock & ClockBoost Features

APEX 20KC devices support the ClockLock and ClockBoost clock management features, which are implemented with PLLs. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost circuitry allows the designer to distribute a low-speed clock and multiply that clock on-device. APEX 20KC devices include a high-speed clock tree; unlike ASICs, the user does not have to design and optimize the clock tree. The ClockLock and ClockBoost features work in conjunction with the APEX 20KC device's high-speed clock to provide significant improvements in system performance and bandwidth. APEX 20KC devices in -7 and -8 speed grades have PLLs and support the ClockLock and ClockBoost features.

The ClockLock and ClockBoost features in APEX 20KC devices are enabled through the Quartus II software. External devices are not required to use these features.

APEX 20KC ClockLock Feature

APEX 20KC devices include up to four PLLs, which can be used independently. Two PLLs are designed for either general-purpose use or LVDS use (on devices that support LVDS I/O pins). The remaining two PLLs are designed for general-purpose use. The EP20K200C devices have two PLLs; the EP20K400C and larger devices have four PLLs.

The following sections describe some of the features offered by the APEX 20KC PLLs.

External PLL Feedback

The ClockLock circuit's output can be driven off-chip to clock other devices in the system; further, the feedback loop of the PLL can be routed off-chip. This feature allows the designer to exercise fine control over the I/O interface between the APEX 20KC device and another high-speed device, such as SDRAM.

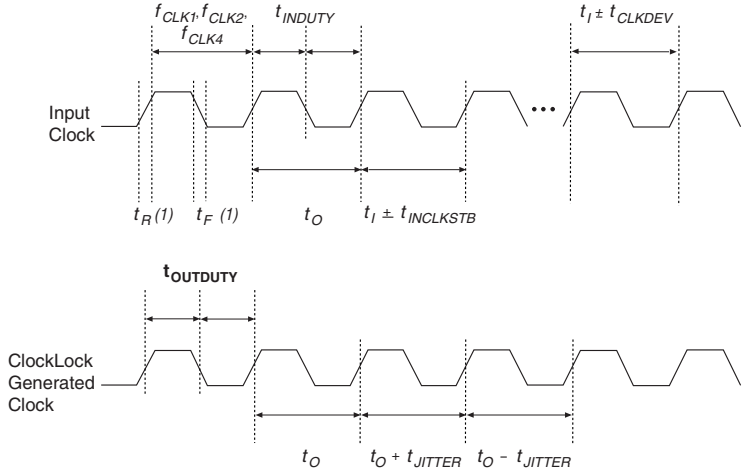
ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the APEX 20KC ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. In APEX 20KC devices, the clock input standard is programmable, so the PLL cannot respond to the clock until the device is configured. The PLL locks onto the input clock as soon as configuration is complete. Figure 29 shows the incoming and generated clock specifications.

For more information on ClockLock and ClockBoost circuitry, see *Application Note 115: Using the ClockLock and ClockBoost PLL Features in APEX Devices*.

Figure 29. Specifications for the Incoming & Generated Clocks

The t_I parameter refers to the nominal input clock period; the t_O parameter refers to the nominal output clock period.



Note to Figure 29:

(1) Rise and fall times are measured from 10% to 90%.

Table 18. APEX 20KC Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(2)*, *(5)*	–0.5	4.1	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time (10% to 90%)			40	ns
t_F	Input fall time (90% to 10%)			40	ns

Table 19. APEX 20KC Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	Input pin leakage current *(8)*	V_I = 3.6 to 0.0 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current *(8)*	V_O = 4.1 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -7 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -8, -9 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(9)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(9)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(9)*	60		150	kΩ

DC operating specifications on APEX 20KC I/O standards are listed in Tables 21 to 35.

Table 22. LVCMOS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Power supply voltage range		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	V_{CCIO} = 3.0 V I_{OH} = –0.1 mA *(1)*	V_{CCIO} – 0.2		V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0 V I_{OL} = 0.1 mA *(2)*		0.2	V

Table 23. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		2.375	2.625	V
V_{IH}	High-level input voltage		1.7	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –0.1 mA *(1)*	2.1		V
		I_{OH} = –1 mA *(1)*	2.0		V
		I_{OH} = –2 mA *(1)*	1.7		V
V_{OL}	Low-level output voltage	I_{OL} = 0.1 mA *(2)*		0.2	V
		I_{OL} = 1 mA *(2)*		0.4	V
		I_{OL} = 2 mA *(2)*		0.7	V

Figure 33. ESB Asynchronous Timing Waveforms

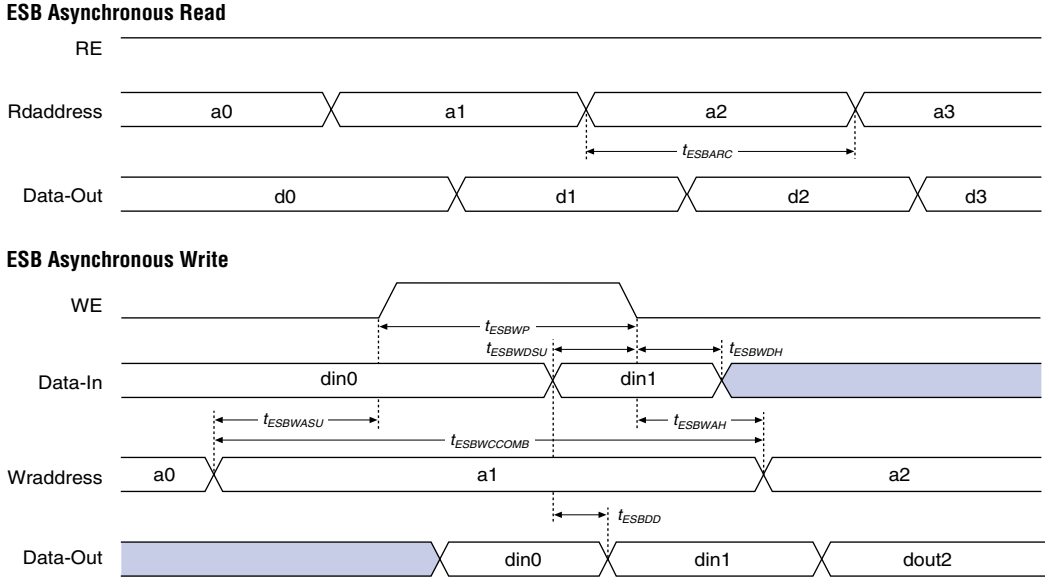


Table 41. APEX 20KC External Bidirectional Timing Parameters Note (1)		
Symbol	**Parameter**	**Condition**
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	(2)
$t_{XZBIDIR}$	Synchronous output enable register to output buffer disable delay	(2)
$t_{ZXBIDIR}$	Synchronous output enable register to output buffer enable delay	(2)
$t_{INSUBIDIRPLL}$	Setup time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{INHBIDIRPLL}$	Hold time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{OUTCOBIDIRPLL}$	Clock-to-output delay for bidirectional pins with PLL clock at IOE register	(2)
$t_{XZBIDIRPLL}$	Synchronous output enable register to output buffer disable delay with PLL	(2)
$t_{ZXBIDIRPLL}$	Synchronous output enable register to output buffer enable delay with PLL	(2)

Notes to Tables 40 and 41:
(1) These timing parameters are sample-tested only.
(2) For more information, refer to Table 43.

Tables 42 and 43 define the timing delays for each I/O standard. Some output standards require test load circuits for AC timing measurements as shown in Figures 36 through 38.

Table 42. APEX 20KC Selectable I/O Standard Input Adder Delays (Part 1 of 2) Note (1)		
Symbol	**Parameter**	**Condition**
LVCMOS	Input adder delay for the LVCMOS I/O standard	
LVTTL	Input adder delay for the LVTTL I/O standard	
2.5 V	Input adder delay for the 2.5-V I/O standard	
1.8 V	Input adder delay for the 1.8-V I/O standard	
PCI	Input adder delay for the PCI I/O standard	
GTl+	Input adder delay for the GTL+ I/O standard	
SSTL-3 Class I	Input adder delay for the SSTL-3 Class I I/O standard	
SSTL-3 Class II	Input adder delay for the SSTL-3 Class II I/O standard	
SSTL-2 Class I	Input adder delay for the SSTL -2 Class I I/O standard	
SSTL-2 Class II	Input adder delay for the SSTL -2 Class II I/O standard	

Table 42. APEX 20KC Selectable I/O Standard Input Adder Delays (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Condition**
LVDS	Input adder delay for the LVDS I/O standard	
CTT	Input adder delay for the CTT I/O standard	
AGP	Input adder delay for the AGP I/O standard	

Table 43. APEX 20KC Selectable I/O Standard Output Adder Delays *Note (1)*		
Symbol	**Parameter**	**Condition**
LVCMOS	Output adder delay for the LVCMOS I/O standard	
LVTTL	Output adder delay for the LVTTL I/O standard	Cload = 35 pF Rup = 564.5 Ω Rdn = 430 Ω *(2)*
2.5 V	Output adder delay for the 2.5-V I/O standard	Cload = 35 pF Rup = 450 Ω Rdn = 450 Ω *(2)*
1.8 V	Output adder delay for the 1.8-V I/O standard	Cload = 35 pF Rup = 520 Ω Rdn = 480 Ω *(2)*
PCI	Output adder delay for the PCI I/O standard	Cload = 10 pF Rup = 1M Ω Rdn = 25 Ω *(2)*
GTl+	Output adder delay for the GTL+ I/O standard	Cload = 30 pF Rup = 25 Ω *(2)*
SSTL-3 Class I	Output adder delay for the SSTL-3 Class I I/O standard	Cload1 = 0 pF Cload2 = 30 pF R = 25 Ω *(2)*
SSTL-3 Class II	Output adder delay for the SSTL-3 Class II I/O standard	Cload1 = 0 pF Cload2 = 30 pF R = 25 Ω *(2)*
SSTL-2 Class I	Output adder delay for the SSTL-2 Class I I/O standard	
SSTL-2 Class II	Output adder delay for the SSTL-2 Class II I/O standard	
LVDS	Output adder delay for the LVDS I/O standard	Cload = 4 pF R=100 Ω *(2)*
CTT	Output adder delay for the CTT I/O standard	
AGP	Output adder delay for the AGP I/O standard	

Note to Tables 42 and 43:

(1) These delays report the differences in delays for different I/O standards. Add the delay for the I/O standard that is used to the external timing parameters.

(2) See Figure 36 for more information.

Table 46. EP20K200C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.17		0.20	ns
t_{F5-20}		0.81		0.94		1.12	ns
t_{F20+}		0.98		1.13		1.35	ns

Table 47. EP20K200C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 48. EP20K200C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.23		1.26		1.33		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	3.79	2.00	4.31	2.00	4.70	ns
$t_{INSUPLL}$	0.81		0.92		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.36	0.50	2.62	-	-	ns

Table 61. EP20K600C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.03		2.57		2.97		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.29	2.00	4.77	2.00	5.11	ns
$t_{XZBIDIR}$		8.31		9.14		9.76	ns
$t_{ZXBIDIR}$		8.31		9.14		9.76	ns
$t_{INSUBIDIRPLL}$	3.99		4.77		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.37	0.50	2.63	-	-	ns
$t_{XZBIDIRPLL}$		6.35		6.94		-	ns
$t_{ZXBIDIRPLL}$		6.35		6.94		-	ns

Table 62. EP20K1000C f_{MAX} LE Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.66		0.79		0.92	ns

Table 65. EP20K1000C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.04		1.26		1.41		ns
t_{ESBRP}	0.87		1.05		1.18		ns

Table 66. EP20K1000C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.14		1.14		1.11		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.63	2.00	5.26	2.00	5.69	ns
$t_{INSUPLL}$	0.81		0.92		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.32	0.50	2.55	-	-	ns